Abstracts

Low-Noise Low-Distortion GaAs FET Amplifiers for 6 GHz Single Sideband Radio

K.K. Agarwal and Y.L. Kuo. "Low-Noise Low-Distortion GaAs FET Amplifiers for 6 GHz Single Sideband Radio." 1978 MTT-S International Microwave Symposium Digest 78.1 (1978 [MWSYM]): 393-395.

This paper describes the design of a single-ended GaAs FET pre-amplifier using both computer aided device modeling and empirical methods. The amplifiers have an average noise figure of 2.3 dB, gain of 9 ± 0.5 dB, third-order distortion (M/sub A+B-C/) of -50 dB and input-output return loss of 30 dB or more over the frequency band of 5.9 to 6.4 GHz.

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